

40V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
	4mΩ @ V _{GS} = 10V	87A
40V	5.5mΩ @ V _{GS} = 4.5V	63A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

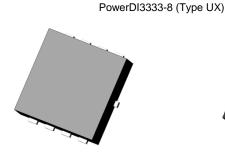
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

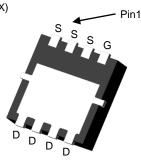
- Low R_{DS(ON)} Ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

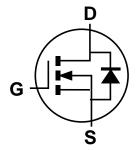
- Case: PowerDI[®]3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.030 grams (Approximate)







Bottom View



Equivalent Circuit

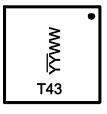
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT43M8LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMT43M8LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	40	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$		ΔD	87 72	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	120	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	56	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	120	Α	
Avalanche Current, L = 1mH (Note 7)	I _{AS}	14	Α	
Avalanche Energy, L = 1mH (Note 7)	E _{AS}	98	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	2.25	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	56	°C/W
Total Power Dissipation (Note 6)		P _D	45.4	W
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	3.3	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

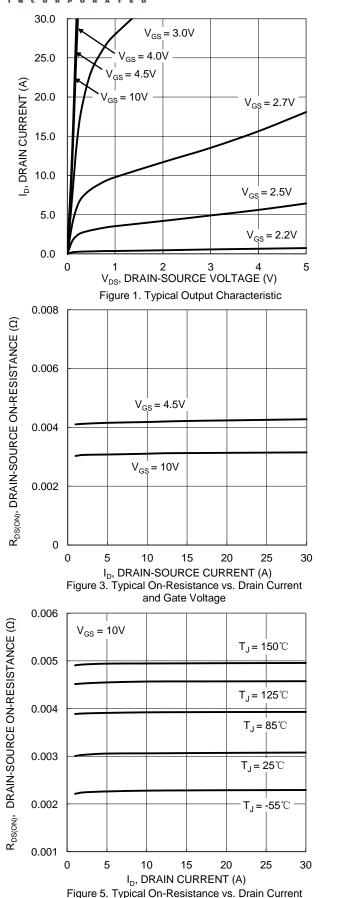
Ch avantaviatio	Complete	Min	T	Mari	Unit	Toot Condition	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)				1		Transaction of the control of the co	
Drain-Source Breakdown Voltage	BV _{DSS}	40		_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I_{DSS}		_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	1		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.6	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	I	3.1	4	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Diani-Source On-Resistance	R _{DS(ON)}	I	4.2	5.5	mr3	$V_{GS} = 4.5V, I_D = 15A$	
Diode Forward Voltage	V_{SD}	-	0.8	1	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	I	3213	_		$V_{DS} = 20V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	l	1108	_	pF		
Reverse Transfer Capacitance	C _{rss}	I	55	_			
Gate Resistance	R_g		2.12	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg		44.4	_			
Total Gate Charge (V _{GS} = 4.5V)	Q_g	I	21.1	_	1		
Gate-Source Charge	Qgs		6.0	_	nC	$V_{DS} = 20V, I_{D} = 20A$	
Gate-Drain Charge	Q_{gd}	_	8.7	_			
Turn-On Delay Time	t _{D(ON)}	_	5.5	_			
Turn-On Rise Time	t _R		8.6	_	ns	$V_{DD} = 20V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	24.9	_	115	$R_G = 1.6\Omega$, $I_D = 20A$	
Turn-Off Fall Time	t _F	_	9.6	_			
Bodyy Diode Reverse Recovery Time	t _{RR}	1	27.6	_	ns	1 15 \ d:/dt 100 \ / / / / / / / / / / / / / / / / / /	
Body Diode Reverse Recovery Charge	Q _{RR}	ı	39.5	_	nC	$I_F = 15A$, di/dt = 400A/ μ s	

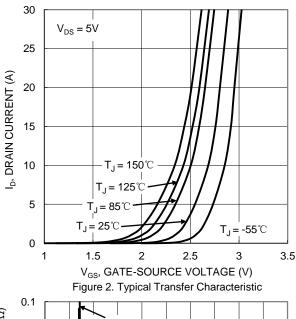
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

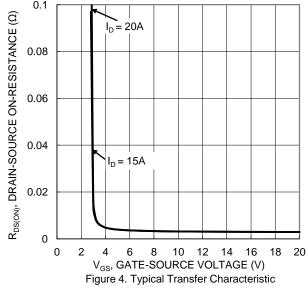
- 6. Thermal resistance from junction to soldering point (on the exposed drain pad). 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

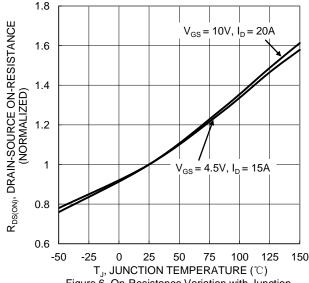












and Junction Temperature





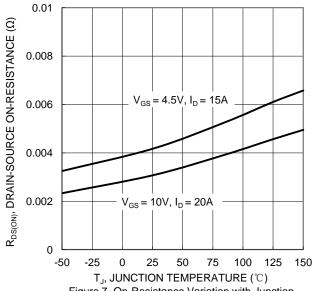
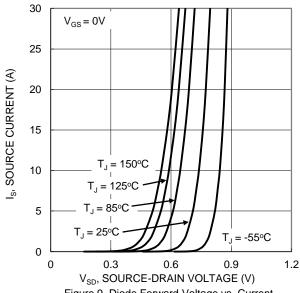
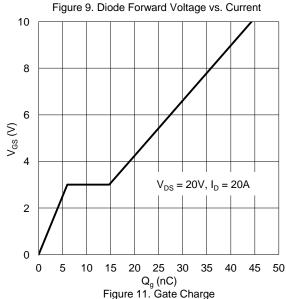


Figure 7. On-Resistance Variation with Junction Temperature





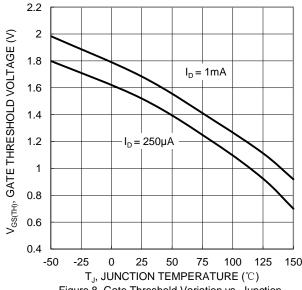
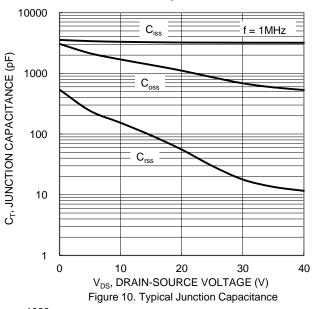
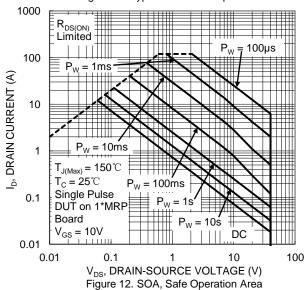


Figure 8. Gate Threshold Variation vs. Junction Temperature







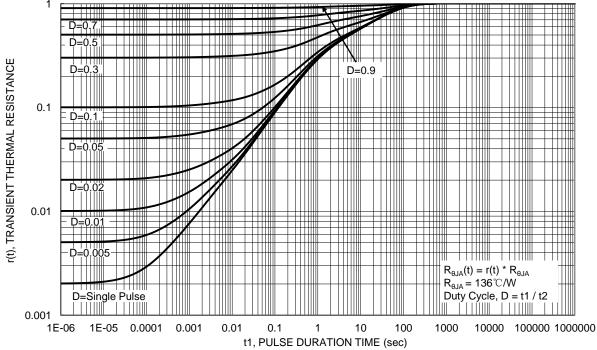


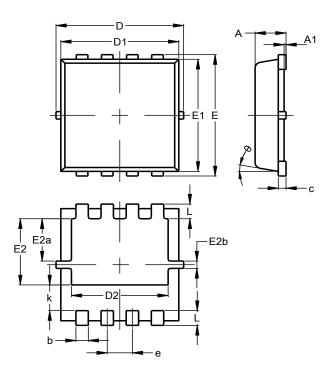
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

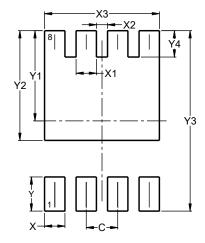


PowerDI3333-8					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
C	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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